

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-13. (Cancelled)

14. (Currently Amended) A method for producing a bonding wafer by the hydrogen ion delamination method, comprising in order;

bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation;

delaminating the base wafer and the bond wafer at the micro bubble layer as a border;

forming an oxide film by subjecting the base wafer having a thin film formed thereon to bonding heat treatment in an oxidizing atmosphere;

masking at least portions of a top surface other than a peripheral portion to be removed; and

removing the peripheral portion of ~~a~~the thin film formed on the base wafer after the delamination step, wherein the removal of the peripheral portion of the thin film is attained by etching the wafer.

15. (Previously Presented) The production method according to Claim 14, wherein the removal of the peripheral portion of the thin film is attained by removing a region of 1-5 mm from the peripheral end of the base wafer.

16. (Previously Presented) The production method according to Claim 14, wherein the thin film has at least an SOI layer, and the removal of the peripheral portion of the thin film is attained by removing at least the SOI layer for a region of 1-5 mm from the peripheral end of the base wafer.

17. (Previously Presented) A method for producing a bonding wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating them at the micro bubble layer as a border, wherein a peripheral portion of a thin film formed on the base wafer is removed after the delamination step, and the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.

18. (Previously Presented) The production method according to Claim 17, wherein the removal of the peripheral portion of the thin film is attained by removing a region of 1-5 mm from the peripheral end of the base wafer.

19. (Previously Presented) The production method according to Claim 17 wherein the thin film has at least an SOI layer, and the removal of the peripheral portion of the thin film is attained by removing at least the SOI layer for a region of 1-5 mm from the peripheral end of the base wafer.

20-24. (Cancelled)